ABSTRACT OF THE DISCLOSURE

There is provided an EL light-emitting device with less uneven brightness.

5 When a drain current of a plurality of current controlling TFTs is Id, a mobility is μ, a gate capacitance per unit area is Co, a maximum gate voltage is Vgs_(max), a channel width is W, a channel length is L, an average value of a threshold voltage is Vth, a deviation from the average value of the threshold voltage is ΔVth, and a difference in emission brightness of a plurality of EL elements is within a range of ±n%, a semiconductor display device is characterized in that

$$A = \frac{2Id}{\mu * C_0}$$

$$\frac{A}{(\text{Vgs}_{(\text{max})} - Vth)^2} \le \frac{W}{L} \le \left(\sqrt{1 + \frac{n}{100}} - 1\right)^2 * \frac{A}{\Delta Vth^2}$$

$$|\Delta Vth| \le (\sqrt{1 + \frac{n}{100}} - 1) * \sqrt{A * L/W}$$